

Williams, K. McDonald, R. A. Weller, S. T. Pantelides, L. C. Feldman, M. K. Das, and J. W. Palmour, "Improved Inversion Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide," IEEE Electron Device Letters accepted for publication; and G. Y. Chung, C. C. Tin, J. R. Williams, K. McDonald, M. Di Ventra, S. T. Pantelides, L. C. Feldman, and R. A. Weller, "Effect of nitric oxide annealing on the interface trap densities near the band edges in the 4H polytype of silicon carbide," Applied Physics Letters, Vol. 76, No. 13, pp. 1713-1715, March 2000. Oxynitrides may be provided as described in United States Patent Application Serial No. [ ]09/878,442, entitled "High Voltage, High Temperature Capacitor Structures and Methods of Fabrication" filed June 11, 2001, the disclosure of which is incorporated herein by reference as if set forth fully herein.

**In the Claims:**

Please cancel the second occurrence of Claim 66 on page 53 at line 24.

Please add the following Claim 90:

90. (New) The method of Claim 61, wherein the third mask is patterned so that the second regions of n-type silicon carbide extend a distance of from about 0.5  $\mu\text{m}$  to about 5  $\mu\text{m}$  from the first regions of n-type silicon carbide to the peripheries of the first regions of p-type silicon carbide.